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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1				Complete if Known		
				Application Number	09/296,835	
				Filing Date	April 22, 1999	
				First Named Inventor	Ronald A. Weimer	
				Art Unit	2813	
				Examiner Name	E. Kielin	
				Attorney Docket Number		M4065.0319/P319

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.*	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code* (if known)			
CK	A	6,063,698	05/16/00	Tseng et al.	
EL	B	6,197,668	03/06/01	Gardner, et al.	
EL	C	US-2001/0020725	09/13/01	Okuno, et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.*	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T*
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*Applicant's unique citation designation number (optional). *See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³
 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.*	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T*
		D	E	F		
EL	D	LU, et al., "Leakage Current Comparison Between Ultra-Thin Ta ₂ O ₅ films and conventional gate dielectrics" IEEE Electron Device Letters 19(9), 9/1998, pp. 341-342				
EL	E	ALERIS, et al., "Intermixing at the Tantalum Oxide/Silicon Interface in Gate Dielectric Structures" Applied Physics Letters 73(11), 14 September 1998, pp. 1517-1519				
EL	F	LUAN, et al., "Ultra-thin High Quality Ta ₂ O ₅ Dielectric Prepared by In-Situ Rapid Thermal Processing" Electron Devices Meeting, held 6-9 December 1998, IEDM '98 Technical Digest, pp. 609-612.				

Examiner Signature	<i>Eric Kielin</i>	Date Considered	8/5/02
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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